PCN Nun	2021	20211111000.2					PCN Date:		ite:	Nov. 19, 2021		
Title:	Qualify UMC12	A for C0	21.4	A Pr	rocess as alt	ernate source	•					
Custome	er Contact:	<u>PCN</u>	Man	nage	<u>er</u>			D	ept:	Qua	lity Services	
Proposed 1 st Ship Date:			19, 2	202	22	Estimated Availabi		_			Date provided at sample request	
Change '	Туре:											
Ass	sembly Site				Design				Wafe	er Bu	mp Site	
Ass	sembly Process				Data Sheet				Wafe	er Bu	mp Material	
Ass	embly Materials				Part numbe	r change			Wafe	er Bu	mp Process	
Med	chanical Specification		Test Site			\boxtimes		Wafer Fab Site				
Pac	king/Shipping/Labelir	ng			Test Process				Wafer Fab Materials			
	☐ Wafer Fab Process									b Process		
	PCN Details											

PCN Deta

Description of Change:

Texas Instruments Incorporated is announcing the qualification of Wafer Fab site UMC12A in the C021.A process as an alternate source.

	Current Fab Site		Alternate Fab Site				
Current Fab Site	Process	Wafer Diameter	New Fab Site	Process	Wafer Diameter		
DMOS6	C021.A	300 mm	UMC12A	C021.A	300 mm		

Process Difference Summary

Description	Current Wafer Fab	Alternate Wafer Fab
Wafer Fab site	DMOS6	UMC12A
Dielectric Material	LK SiOC/TEOS (k value = 3.1)	LK SiOC (k value = 3.1)
Top Protective Layer or Passivation Layer Material	PO Oxide (TEOS/SiON)	TEOS/SiN

Reason for Change:

Continuity of Supply.

Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current:

Current Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DMOS6	DM6	USA	Dallas

New Fab Site:

New Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
UMC12A	F12	TWN	Tainan

Sample Product Shipping Label (not actual product label)





(1P) \$N74L\$07N\$R

(Q) 2000 (D) 0336

(31T)LOT: 3959047MLA

(4W) TKY(1T) 7523483\$I2

(P)

(2P) REV: (V) 0033317

(20L) C\$0: SHE (21L) CCO: U\$A

(22L) A\$0: MLA (23L) ACO: MY\$

Product Affected:

DP83TC811RWRNDRQ1 DP83TC811RWRNDTQ1 DP83TC811SWRNDRQ1 DP83TC811SWRNDTQ1

Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Approved 27-October-2021 **Product Attributes**

Attributes	Qual Device: DP83TC811RWRNDRQ1	QBS Process Reference: DS90UB964TRGCRQ1	QBS Product Reference: PDP83TC811RWRNDRQ1	QBS Package Reference: DS90UB960WRTD	QBS Package Reference: DS90UH949TRGCRQ1	
Automotive Grade Level	Grade 1	Grade 2	Grade 1	Grade 2	Grade 2	
Operating Temp Range	-40 to +125 C	-40 to +105 C	-40 to +125 C	-40 to +105 C	-40 to +105 C	
Wafer Fab Supplier	UMC12A	UMC12A	DMOS6	DMOS6	DMOS6	
Die Revision	A1	A1	A0	A0	A	
Assembly Site	AP1	CLARK AT	AP1	AP1	CLARK AT	
Package Type	VQFN	VQFN	VQFN	VQFN	VQFN	
Package Designator	RND	RGC	RND	RTD	RGC	
Ball/Lead Count	36	64	36	64	64	

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Mi n Lo t Qt	SS / Lo t	Test Name / Condition	Duratio n	Qual Device: DP83TC811RW RNDRQ1	QBS Process Reference: DS90UB964TRGCR Q1	QBS Prodeuct Reference: PDP83TC811RWR NDRQ1	QBS Package Reference: DS90UB960WRTD	QBS Package Reference: DS90UH949 TRGCRQ1
						Test Grou	ıp A – Accelerated E	nvironment Stress Tests			
PC	A 1	JEDEC J-STD- 020 JESD22 -A113	3	77	Automotive Preconditionin g	Level 3- 260C	-	3/Pass	3/1058/0	2/Pass	1/Pass
HAST	A 2	JEDEC JESD22 -A110	3	77	Biased HAST, 110C/85%RH	528 Hours	-	3/231/0	-	-	-
HAST	A 2	JEDEC JESD22 -A110	3	77	Biased HAST, 130C/85%RH	96 Hours	-	-	3/231/0	2/154/0	1/77/0
HAST	A 2	JEDEC JESD22 -A110	3	77	Biased HAST, 130C/85%RH	192 Hours	-	-	-	2/154/0	1/77/0
AC	A 3	JEDEC JESD22 -A102	3	77	Autoclave 121C	192 Hours	-	-	3/231/0	2/154/0	1/77/0
UHAS T	A 3	JEDEC JESD22 -A118	3	77	Unbiased HAST, 110C/85%RH	264 Hours	-	3/231/0	-	1	-
UHAS T	A 3	JEDEC JESD22 -A118	3	77	Unbiased HAST, 130C/85%RH	96 Hours	-	-	-	1	-
TC	A 4	JEDEC JESD22 -A104 and Append ix 3	3	77	Temperature Cycle, - 65/150C	500 Cycles	,	3/231/0	3/231/0	2/154/0	1/77/0

⁻ QBS: Qual By Similarity - Qual Devices qualified at LEVEL3-260C: DS90UB934TRGZRQ1

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	TC	A 4	JEDEC JESD22 -A104 and Append ix 3	3	77	Temperature Cycle, - 65/150C	1000 Cycles	-	3/219/0	-	2/154/0	1/77/0
	TC- BP	A 4	JEDEC JESD22 -A104 and Append ix 3	3	77	Post Temp. Cycle, Bond Pull	Wires	-	1/30/0	3/15/0	1/3/0	-
	PTC	A 5	JEDEC JESD22 -A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	NA	N/A	NA	NA
	HTSL	A 6	JEDEC JESD22 -A103	1	45	High Temp Storage Bake 150C	500 Hours	-	-	-	-	-
	HTSL	A 6	JEDEC JESD22 -A103	1	45	High Temp Storage Bake 150C	1000 Hours	-	1/45/0	-	2/90/0	1/45/0
	HTSL	A 6	JEDEC JESD22 -A103	1	45	High Temp Storage Bake 175C	1000 Hours	-	-	3/231/0		
							Test Gro	up B – Accelerated L	ifetime Simulation Tests			
	HTOL	B 1	JEDEC JESD22 -A108	3	77	Life Test, 125	1000 Hours	1/77/0	3/231/0	3/231/0	3/231/0	-
	ELFR	B 2	AEC Q100- 008	3	80 0	Early Life Failure Rate, 125C	24 Hours	-	3/2400/0			-
	EDR	B 3	AEC Q100- 005	3	77	NVM Endurance, Data Retention, and Operational Life		N/A	N/A	N/A	N/A	N/A
							Test Gi	oup C – Package As	sembly Integrity Tests			
	WBS	C 1	AEC Q100- 001	1	30	Bond Shear (Cpk>1.67)	Wires	1/30/0	1/30/0	3/30/0	3/90/0	-
	WBP	C 2	MIL- STD88 3 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0	1/30/0	3/30/0	3/90/0	-
	SD	C 3	JEDEC JESD22 -B102	1	15	Surface Mount Solderability >95% Lead Coverage	8 Hours Steam Age	-	-	3/90/0	3/90/0	-
	PD	C 4	JEDEC JESD22 -B100 and B108	3	10	Physical Dimensions (Cpk>1.67)		-	3/90/0	3/30/0	3/90/0	-
							Test G	roup D – Die Fabric	ation Reliability Tests			
	EM	D 1	JESD61	-	-	Electromigrati on		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirement s
	TDDB	D 2	JESD35	-	-	Time Dependant Dielectric Breakdown		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirement s
	НСІ	D 3	JESD60 & 28	-	-	Hot Injection Carrier	1	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirement s
	NBTI	D 4	-	-	-	Negative Bias Temperature Instability		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirement s
	SM	D 5	-	-	-	Stress Migration		Completed Per Process	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process

							Technology Requirements	Requirements	Requirements	Requirements	Technology Requirement s
						Test	Group E – Electrica	al Verification Tests			
НВМ	E 2	AEC Q100- 002	1	3	ESD - HBM	2000 V	1/3/0	1/3/0	1/3/0	-	-
CDM	E 3	AEC Q100- 011	1	3	ESD - CDM	1000 V	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
LU	E 4	AEC Q100- 004	1	6	Latch-up	(Per AEC Q100- 004)	1/6/0	1/6/0	1/6/0	1/6/0	1/6/0
ED	E 5	AEC Q100- 009	3	30	Auto Electrical Distributions	Cpk>1.6 7	3/90/0	3/90/0	3/90/0	3/90/0	3/90/0

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

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